

**AMENDMENTS TO THE ABSTRACT**

Please replace the existing Abstract with the following new Abstract filed herewith and submitted on a separate sheet (37 CFR 1.72). Please cancel the existing abstract.

Attachment: New Abstract of the Disclosure (clean text)

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**ABSTRACT OF THE DISCLOSURE**

A semiconductor laser includes semiconductor layers stacked on a substrate, and a pair of resonator end surfaces opposed to each other in the direction perpendicular to the stacking direction. In this semiconductor laser, a light emission side reflecting film is formed on one of the resonator end surfaces. A refractive index of the reflecting film against an emission wavelength of laser light is set to a value between an effective refractive index and a refractive index of the substrate.

Another semiconductor laser includes a light emission function layer stack including a cladding layer and an active layer formed on one place of a translucent substrate; two electrodes having different polarities, which are provided on the light emission function layer stack side; and a light leakage preventive film formed on the other plane of the translucent substrate.